NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ZTX692B

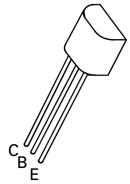
ISSUE 1 – APRIL 94

FEATURES

- 70 Volt V_{CEO}
- Gain of 400 at I_C=500mA
- Very low saturation voltage

APPLICATIONS

- Darlington replacement
- Relay drivers
- Battery powered circuits
- Motor drivers



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	70	V
Collector-Emitter Voltage	V_{CEO}	70	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation at T_{amb}=25°C derate above 25°C	P_{tot}	1 5.7	W mW/°C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200	°C

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	70			V	I_C=100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	70			V	I_C=10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	I_E=100μA
Collector Cut-Off Current	I_{CBO}			0.1	μA	V_{CB}=55V
Emitter Cut-Off Current	I_{EBO}			0.1	μA	V_{EB}=4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.15 0.5	V V	I_C=0.1A, I_B=0.5mA* I_C=1A, I_B=10mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	I_C=1A, I_B=10mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	IC=1A, V_{CE}=2V*
Static Forward Current Transfer Ratio	h_{FE}	500 400 150				I_C=100mA, V_{CE}=2V* I_C=500mA, V_{CE}=2V* I_C=1A, V_{CE}=2V*

ZTX692B

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

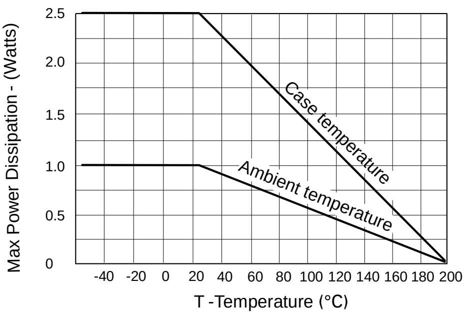
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	150			MHz	I_C=50mA, V_{CE}=5V f=50MHz
Input Capacitance	C_{ibo}		200		pF	V_{EB}=0.5V, f=1MHz
Output Capacitance	C_{obo}		12		pF	V_{CB}=10V, f=1MHz
Switching Times	t_{on} t_{off}		46 1440		ns ns	I_C=500mA, I_{B1}=50mA I_{B2}=50mA, V_{CC}=10V

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

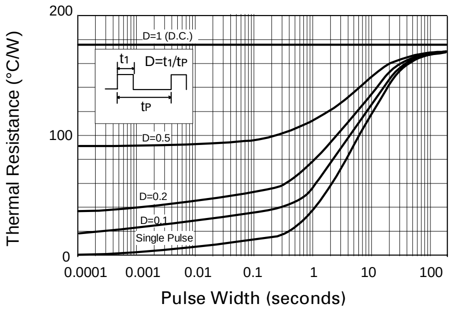
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance:Junction to Ambient$_1$ Junction to Ambient$_2$ Junction to Case	$R_{th(j-amb)1}$ $R_{th(j-amb)2}$† $R_{th(j-case)}$	175 116 70	°C/W °C/W °C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

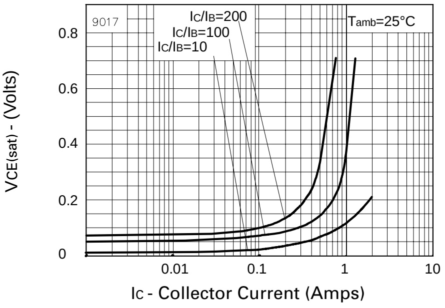


Derating curve

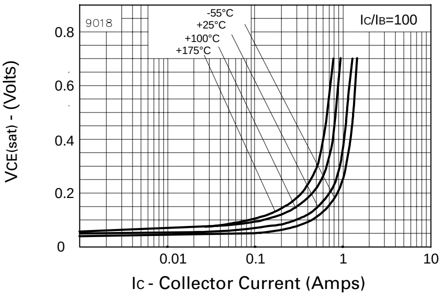


Maximum transient thermal impedance

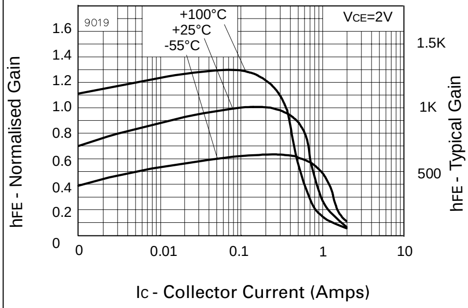
TYPICAL CHARACTERISTICS



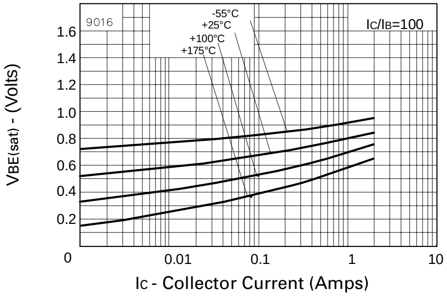
$V_{CE(sat)}$ v I_C



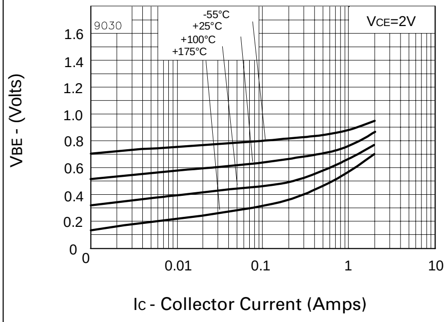
$V_{CE(sat)}$ v I_C



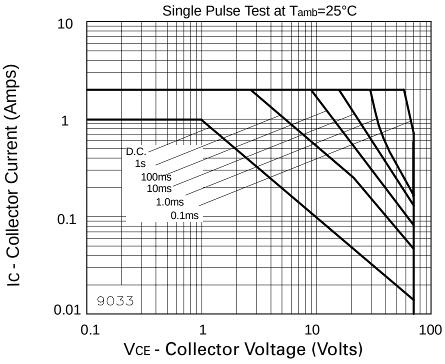
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area